L Number	Hits	Search Text	DB	Time stamp
1	1175		USPAT;	2002/12/08 12:17
-	11,5	dop\$3 and crystalliz\$5	EPO; JPO;	2002/12/00 12:17
		dopts and crystallizes	DERWENT	†
2	34	radiat\$3 same amorphous same silicon same	USPAT;	2002/12/08 12:12
2	34	dop\$3 same crystalliz\$5	· ·	2002/12/08 12:12
		dop\$3 same crystalliz\$5	EPO; JPO;	
_		4 - 3 - 4 - 6 - 6 - 6 - 6 - 6 - 6 - 6 - 6 - 6	DERWENT	0000/10/00 10 10
3	12	(radiat\$3 same amorphous same silicon same	USPAT;	2002/12/08 12:12
		dop\$3 same crystalliz\$5) same gate	EPO; JPO;	
			DERWENT	
4	350	radiat\$3 and amorphous and silicon and	USPAT;	2002/12/08 12:22
		dop\$3 and crystalliz\$5 and (gate with	EPO; JPO;	
+	ŀ	dop\$3)	DERWENT	
5	315	(radiat\$3 and amorphous and silicon and	USPAT;	2002/12/08 12:20
		dop\$3 and crystalliz\$5 and (gate with	EPO; JPO;	
		dop\$3)) and laser	DERWENT	
6	181	((radiat\$3 and amorphous and silicon and	USPAT;	2002/12/08 12:21
Ŭ	101	dop\$3 and crystalliz\$5 and (gate with	EPO; JPO;	2002/12/00 12:21
_	101	dop\$3)) and laser) and 438/\$3.ccls.	DERWENT	0000/10/00 10 01
7	181	(((radiat\$3 and amorphous and silicon and	USPAT;	2002/12/08 12:21
		dop\$3 and crystalliz\$5 and (gate with	EPO; JPO;	
		dop\$3)) and laser) and 438/\$3.ccls.) and	DERWENT	4
		@ad<20010829		
8	33	radiat\$3 and amorphous and silicon and	USPAT;	2002/12/08 12:59
		dop\$3 and crystalliz\$5 and (gate with	EPO; JPO;	
		dop\$3 with amorphous)	DERWENT	
9	4		USPAT;	2002/12/08 13:04
		dop\$3 with amorphous)	EPO; JPO;	
		· · ·	DERWENT	
10	2	radiat\$3 same amorphous same (crystalliz\$5	USPAT;	2002/12/08 13:08
10	-	with gate with dop\$3)	EPO; JPO;	2002/12/00 13:00
į		with gate with dopps,	DERWENT	
11	11	wadist\$2 came amountous same amountallis\$5		2002/12/00 12-20
11	11		USPAT;	2002/12/08 13:30
		same (gate with dop\$3)	EPO; JPO;	
			DERWENT	
12	28	anneal\$3 same crystalliz\$5 same (amorphous	USPAT;	2002/12/08 15:51
j		with gate with dop\$3)	EPO; JPO;	
			DERWENT	
13	3	("5872761" "5994179" "6054355").PN.	USPAT	2002/12/08 14:00
14	11	gate with height with "500" with	USPAT;	2002/12/08 15:55
		(nanometer\$1 or nm)	EPO; JPO;	
			DERWENT	
15	62	gate with height with ("400" or "300" or	USPAT;	2002/12/08 15:56
		"200" or "100") with (nanometer\$1 or nm)	EPO; JPO;	
		,	DERWENT	
_	213204	257/\$3.ccls. or 438/\$3.ccls.	USPAT;	2002/12/08 11:42
	213201	20,7,43.0013. 01 130,43.0013.	EPO; JPO;	2002/12/00 11:12
			DERWENT	
· _	6	(257/\$3.ccls. or 438/\$3.ccls.) and	USPAT;	2002/04/09 09:46
	•			2002/04/09 09:46
		insulat\$3 and radiat\$3 and (amorphous	EPO; JPO;	
		near2 silicon) and crystall\$7 and	DERWENT	
	_	explosive		0000461400 55 55
-	1	(257/\$3.ccls. or 438/\$3.ccls.) and (xcr or	USPAT;	2002/04/09 09:58
		(explosive adj recrystallization)) and	EPO; JPO;	
		irradiat\$3 and dopant and gate	DERWENT	
	103		USPAT;	2002/04/09 09:59
		recrystallization and irradiat\$3 and	EPO; JPO;	
		dopant and gate	DERWENT	
-	85	((257/\$3.ccls. or 438/\$3.ccls.) and	USPAT;	2002/04/09 15:19
		recrystallization and irradiat\$3 and	EPO; JPO;	
		dopant and gate) and (amorphous adj	DERWENT	
		silicon)		
_	3	mosfet same (laser or irradiate) same	USPAT;	2002/04/09 16:11
1]	amorphous same (dopant or dope)	EPO; JPO;	2502,01,05 10.11
		amorphous same (dopant or dope)	DERWENT	1
_	111	/lacor or irradiatel same (amenubaca sat		2002/04/10 16:52
-	111	(laser or irradiate) same (amorphous adj	USPAT;	2002/04/10 16:52
-	111	(laser or irradiate) same (amorphous adj silicon) same (dopant or dope)	USPAT; EPO; JPO;	2002/04/10 16:52
-		silicon) same (dopant or dope)	USPAT; EPO; JPO; DERWENT	
-	111	silicon) same (dopant or dope) ((laser or irradiate) same (amorphous adj	USPAT; EPO; JPO; DERWENT USPAT;	2002/04/10 16:52
-		silicon) same (dopant or dope)	USPAT; EPO; JPO; DERWENT	

-	241	mosfet with laser	USPAT;	2002/04/09 17:50
			EPO; JPO;	
			DERWENT	
_	2	1	USPAT;	2002/04/09 17:52
		silicon)	EPO; JPO;	
	12	(mosfet with laser) same (dope dopant	DERWENT USPAT;	2002/04/09 18:06
_	12	doped)	EPO; JPO;	2002/04/09 18:06
		doped,	DERWENT	
_	42	(mosfet with laser) and ((dope dopant	USPAT;	2002/04/09 18:07
		doped) with gate)	EPO; JPO;	
			DERWENT	
-	12557	(mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10 17:18
		gate	EPO; JPO;	
			DERWENT	
-	158	((mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10 11:07
		gate) same (laser or irradiation)	EPO; JPO;	
	4	#E06660E#	DERWENT	2002/04/10 11 07
-	4	"5966605"	USPAT;	2002/04/10 11:07
!			EPO; JPO; DERWENT	
_	54793	gate with silicon	USPAT;	2002/04/10 14:12
	51755	duce with billoon	EPO; JPO;	2002/04/10 14:12
			DERWENT	
_	6957	((mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10 14:12
]		gate) and (gate with silicon)	EPO; JPO;	
}		-	DERWENT	
-	15744	gate near2 silicon	USPAT;	2002/04/10 14:12
			EPO; JPO;	İ
			DERWENT	
-	2731	((mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10 14:12
		gate) and (gate near2 silicon)	EPO; JPO;	
1	024	///	DERWENT	0000/04/10 14 15
-	234	(((mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10 14:15
		gate) and (gate near2 silicon)) and (laser or irradiate)	EPO; JPO; DERWENT	
_	110	((((mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10 16:15
	110	gate) and (gate near2 silicon)) and (laser	EPO; JPO;	2002/04/10 10:13
		or irradiate)) and amorphous and	DERWENT	
		(recrystallize or polycrystalline or		
		crystalline)		
-	13	"5937325"	USPAT;	2002/04/10 16:19
	7		EPO; JPO;	
		H C 0 1 2 0 0 0 W	DERWENT	0000/04/00 16 00
h-	8	"6013928"	USPAT;	2002/04/10 16:20
			EPO; JPO; DERWENT	
_	34	(laser or irradiate) same (amorphous adj	USPAT;	2002/04/10 16:53
	54	silicon) same ((dopant or dope) and	EPO; JPO;	2002,01,10 10.00
[]		(sputter or deposition or evaporation))	DERWENT	
-	3488	(mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10 17:20
		gate same (sputter or evaporat\$3 or	EPO; JPO;	
		deposit\$3)	DERWENT	
-	3958	((mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10 17:21
		gate) and (dop\$3 with (sputter or	EPO; JPO;	
	1.55	deposit\$3 or evaporat\$3))	DERWENT	2002/04/10 17 01
_	137	((mosfet or fet or mos) same dop\$3 same	USPAT; EPO; JPO;	2002/04/10 17:21
		<pre>gate) and (dop\$3 with (sputter or evaporat\$3))</pre>	DERWENT	
_	41		USPAT;	2002/04/10 17:25
	41	gate) same (dop\$3 with (sputter or	EPO; JPO;	
		evaporat\$3))	DERWENT	
-	75		USPAT;	2002/04/10 17:32
		gate) same (dop\$3 with (sputter\$3 or	EPO; JPO;	
1		evaporat\$3))	DERWENT	
-	320	(dop\$3 with (sputter\$3 or evaporat\$3) with	USPAT;	2002/04/10 17:46
	J 15	silicon) and (mos or fet or mosfet)	EPO; JPO;	
			DERWENT	0000/5:/55 5= 5=
-	35	(dop\$3 with (sputter\$3 or evaporat\$3) with	USPAT;	2002/04/10 17:35
[silicon) same (mos or fet or mosfet)	EPO; JPO;	
	L		DERWENT	

	28	(dop\$3 with (sputter\$3 or evaporat\$3) with	USPAT;	2002/04/10 17:51
_	20	silicon) same laser	EPO; JPO;	2002/04/10 17:51
_	190	(dop\$3 with (sputter\$3 or evaporat\$3))	DERWENT USPAT;	2002/04/10 18:02
	150	same laser	EPO; JPO;	2002/04/10 10:02
			DERWENT	
-	2	"6165875"	USPAT;	2002/04/10 18:02
			EPO; JPO;	
			DERWENT	
-	2848	gate with (metal or cap or capped) with	USPAT;	2002/04/11 16:14
		(tungsten or tantalum or titanium or platinum)	EPO; JPO; DERWENT	
_	331	(gate with (metal or cap or capped) with	USPAT;	2002/04/11 16:20
	331	(tungsten or tantalum or titanium or	EPO; JPO;	2002/04/11 10.20
		platinum)) and laser	DERWENT	
_	89	(gate with (metal or cap or capped) with	USPAT;	2002/04/11 16:20
		(tungsten or tantalum or titanium or	EPO; JPO;	
		platinum)) and laser and mosfet	DERWENT	
_	4	"6077758"	USPAT;	2002/04/11 17:34
			JPO;	
	11067		DERWENT	2002/04/15 14 06
_	11867	(boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or evaporat\$3)	USPAT;	2002/04/15 14:06
		with (sputters) of CVD of evaporates)	EPO; JPO; DERWENT	
_	12	((boron or indium or arsenic or	USPAT;	2002/04/15 14:02
	12	phosphorus) with (sputter\$3 or CVD or	EPO; JPO;	2002/04/13 14.02
		evaporat\$3)) same dopant same laser	DERWENT	
_	1098	((boron or indium or arsenic or	USPAT;	2002/04/15 15:10
		phosphorus) near2 layer) with (sputter\$3	EPO; JPO;	
		or CVD or evaporat\$3)	DERWENT	
-	33		USPAT;	2002/04/15 14:09
		phosphorus) near2 layer) with (sputter\$3	EPO; JPO;	
	239	or CVD or evaporat\$3)) same dopant ((boron or indium or arsenic or	DERWENT	2002/04/15 15.12
_	239	phosphorus) near2 layer) with (sputter\$3	USPAT; EPO; JPO;	2002/04/15 15:13
		or CVD or evaporat\$3) with surface	DERWENT	
_	46		USPAT;	2002/04/15 15:14
		phosphorus) near2 layer) with (sputter\$3	EPO; JPO;	
	:	or CVD or evaporat\$3) with surface) and	DERWENT	
		laser		
-	2	5966605.pn.	USPAT;	2002/09/13 13:14
			EPO; JPO;	
		6265476	DERWENT	2002/00/12 12 15
-	2	6365476.pn.	USPAT;	2002/09/13 13:15
			EPO; JPO; DERWENT	
_	2	6274488.pn.	USPAT;	2002/09/13 13:16
		om,	EPO; JPO;	2002/03/13 13.10
			DERWENT	
_	2	6077758.pn.	USPAT;	2002/09/13 13:16
			EPO; JPO;	
}			DERWENT	